

isc Silicon NPN Power Transistor
2SC1185
DESCRIPTION

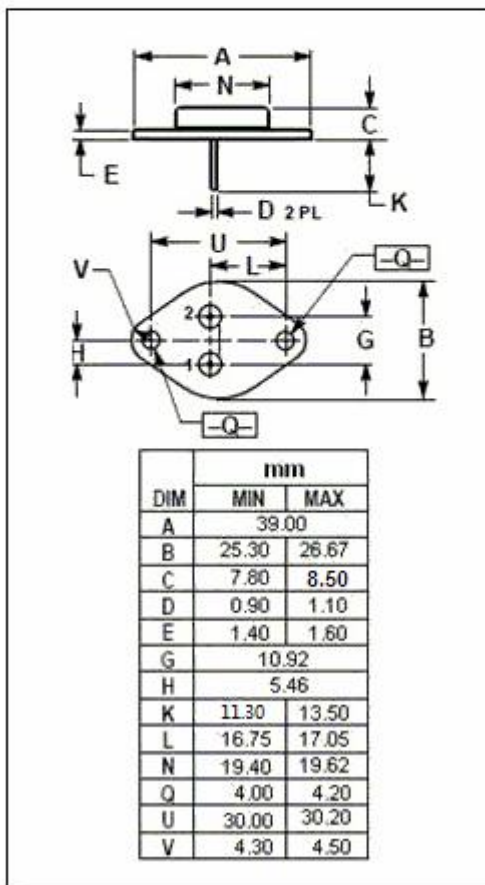
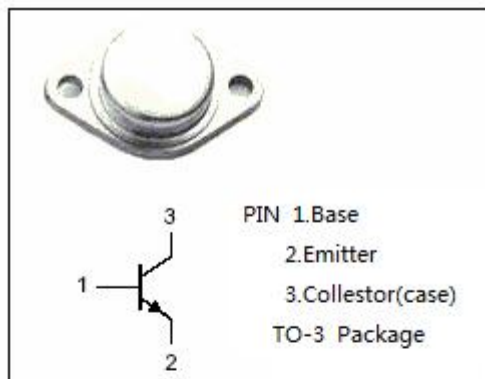
- With TO-3 Package
- High voltage
- Wide area of safe operation
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For power amplifier applications

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{CBO}	Collector-Base Voltage	300	V
V _{CEO}	Collector-Emitter Voltage	250	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current-Continuous	0.7	A
P _C	Collector Power Dissipation	50	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _c =0.5A; I _B = 0.1A			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _c =0.5A; I _B = 0.1A			1.5	V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _c = 25mA; I _B = 0	250			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA; I _c = 0	5			V
h _{FE}	DC Current Gain	I _c =0.4A; V _{CE} = 10V	40		200	

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